

# **Notice of References Cited**

Application/Control No. <b>09/658,732</b>		Applicant(s)/Patent Under Reexam <b>Inai et al.</b>	
Examiner <b>B. William Baumeister</b>		Art Unit <b>2815</b>	Page 1 of 1

## **U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>
A				
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## **FOREIGN PATENT DOCUMENTS**

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N					
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P					
Q					
R					
S					
T					

## **NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Enoki, "Delay Time Analysis for 0.4- to 5-micron-Gate InAlAs-InGaAs HEMT's," IEEE Electron Device Letters 11 (1990) November, No. 11, pp. 502-504.
V	
W	
X	

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